

NOT RECOMMENDED FOR NEW DESIGN USE DMN2058U



DMG3420U

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
20V	$29m\Omega$ @ $V_{GS} = 10V$	6.5A
	$35m\Omega$ @ $V_{GS} = 4.5V$	5.2A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

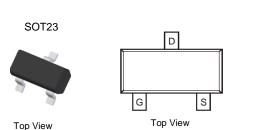
- General Purpose Interfacing Switch
- Power Management Functions

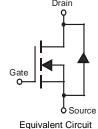
Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (©3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)





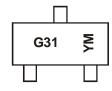
Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMG3420U-7	Standard	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4.. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



G31 = Product Type Marking Code YM or \overline{Y} M = Date Code Marking Y or \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2009	~	2019	2020	202	21 20)22 2	2023	2024	2025	2026	2027
Code	W	?	G	Н			J	K	L	M	N	0
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characte		Symbol	Value	Unit	
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 5)	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I _D	5.47 3.43	Α
Pulsed Drain Current (Note 6)		I _{DM}	20	Α	

Thermal Characteristics

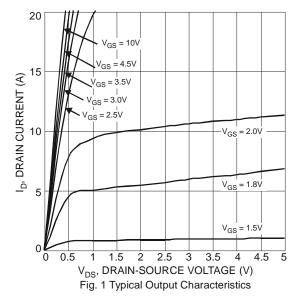
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.74	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{\theta JA}$	167	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

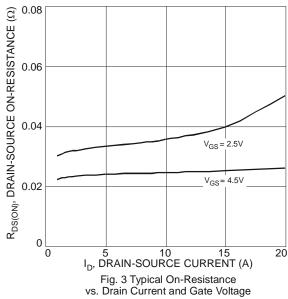
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

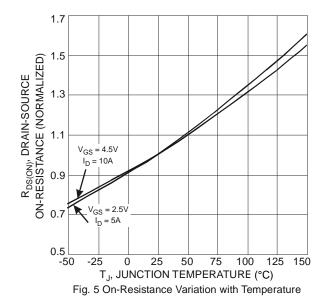
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)				•	•	•
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						•
Gate Threshold Voltage	V _{GS(TH)}	0.5	0.95	1.2	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
			21	29		$V_{GS} = 10V, I_D = 6A$
Static Drain-Source On-Resistance	D.		25	35	mΩ	$V_{GS} = 4.5V, I_D = 5A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	34	48		$V_{GS} = 2.5V, I_D = 4A$
			65	91		$V_{GS} = 1.8V, I_D = 2A$
Forward Transfer Admittance	Y _{fs}	_	9	_	S	$V_{DS} = 5V, I_{D} = 3.8A$
Diode Forward Voltage	V _{SD}	_	0.75	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 8)				•	•	
Input Capacitance	C _{iss}	_	434.7	_	pF	
Output Capacitance	Coss	-	69.1	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C_{rss}	_	61.2	_	pF	1 = 1.00012
Gate Resistance	Rg	_	1.53	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Q_g	_	5.4	_	nC	
Gate-Source Charge	Q _{gs}	_	0.9	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 6A$
Gate-Drain Charge	Q_{gd}		1.5	_	nC	ID = 0A
Turn-On Delay Time	t _{D(ON)}		6.5	_	ns	
Turn-On Rise Time	t _R	_	8.3	_	ns	$V_{DD} = 10V, V_{GS} = 5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	21.6	_	ns	$R_L = 1.7\Omega$, $R_g = 6\Omega$
Turn-Off Fall Time	t _F		5.3	_	ns	7

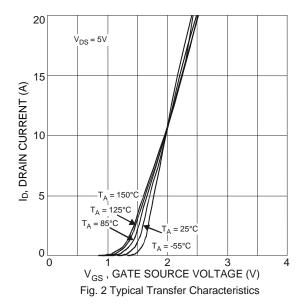
Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.









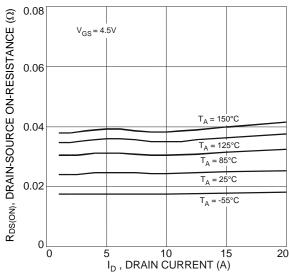


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

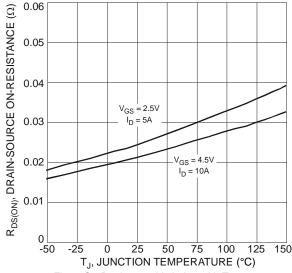


Fig. 6 On-Resistance Variation with Temperature



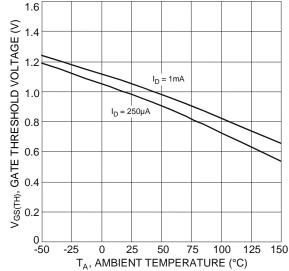
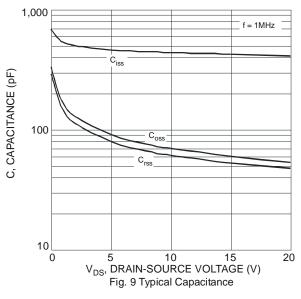
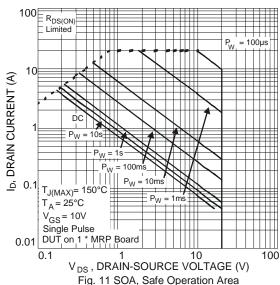
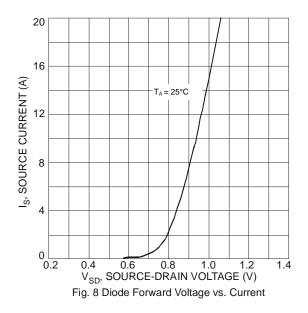
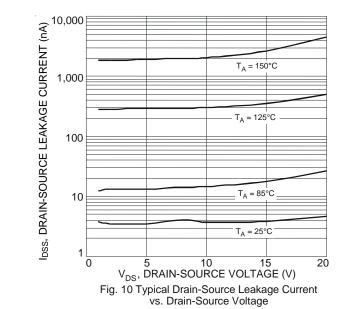


Fig. 7 Gate Threshold Variation vs. Ambient Temperature









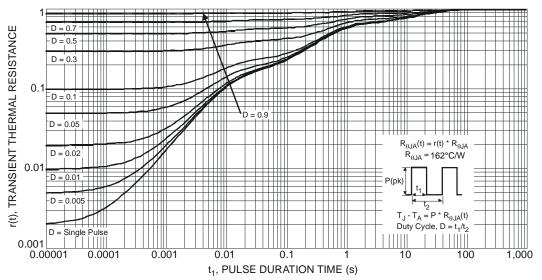
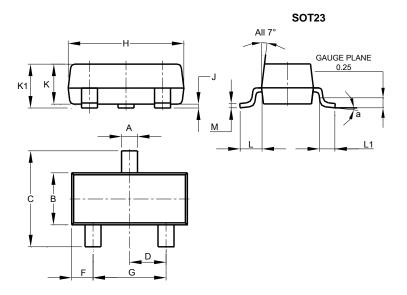


Fig. 12 Transient Thermal Response

Package Outline Dimensions

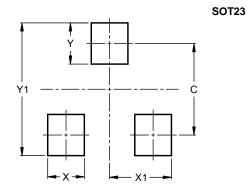
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	29



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